High-Performance Notebook PWM Controller

Features

- **Adjustable Output Voltage from +0.75V to +5.5V**
  - **0.75V Reference Voltage**
  - **±1% Accuracy Over-Temperature**
- **Operates from An Input Battery Voltage Range of +1.8V to +28V**
- **Power-On-Reset Monitoring on VCC Pin and PVCC Pin**
- **Excellent Line and Load Transient Responses**
- **PFM Mode for Increased Light Load Efficiency**
- **Programmable PWM Frequency from 100kHz to 500kHz**
- **Integrated MOSFET Drivers**
- **Integrated Bootstrap Forward P-CH MOSFET**
- **Adjustable Integrated Soft-Start and Soft-Stop**
- **Selectable Forced PWM or Automatic PFM/PWM Mode**
- **Power Good Monitoring**
- **70% Under-Voltage Protection**
- **125% Over-Voltage Protection**
- **Adjustable Current-Limit Protection**
  - **Using Sense Low-Side MOSFET's $R_{DS(ON)}$**
- **Over-Temperature Protection**
- **TSSOP-14, QFN3.5x3.5-14, and TQFN3x3-16 Packages**
- **Lead Free and Green Devices Available (RoHS Compliant)**

Applications

- **Notebook**
- **Table PC**
- **Hand-Held Portable**
- **AIO PC**

General Description

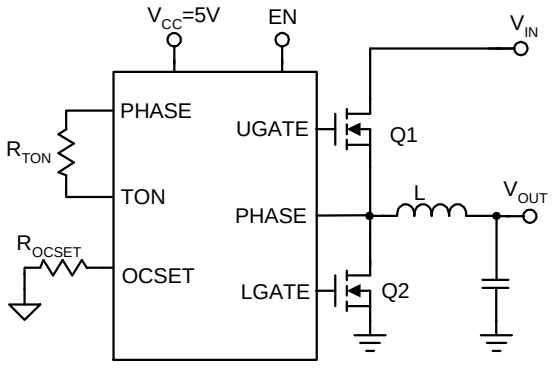
The APW8815 is a single-phase, constant-on-time, synchronous PWM controller, which drives N-channel MOSFETs. The APW8815 steps down high voltage to generate low-voltage chipset or RAM supplies in notebook computers.

The APW8815 provides excellent transient response and accurate DC voltage output in either PFM or PWM Mode. In Pulse Frequency Mode (PFM), the APW8815 provides very high efficiency over light to heavy loads with loading-modulated switching frequencies. In PWM Mode, the converter works nearly at constant frequency for low-noise requirements.

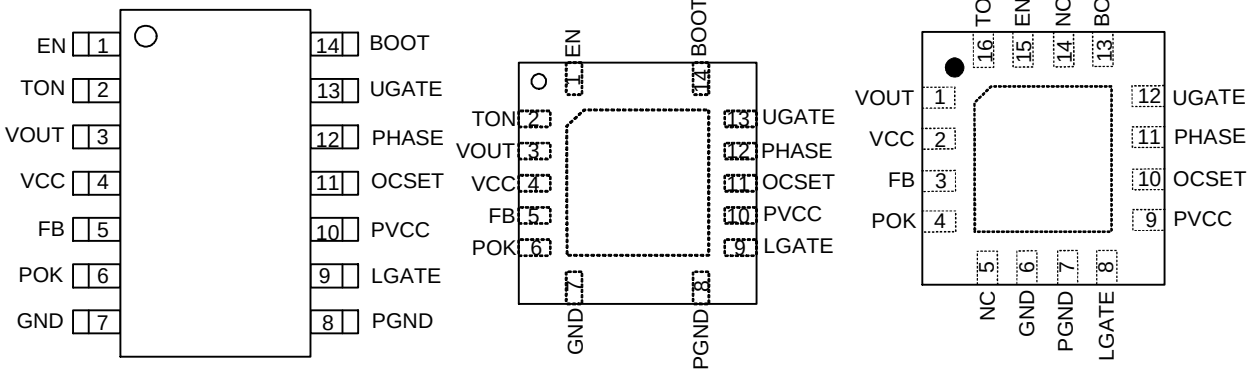
The APW8815 is equipped with accurate positive current-limit, output under-voltage, and output over-voltage protections, perfect for NB applications. The Power-On-Reset function monitors the voltage on VCC and PVCC to prevent wrong operation during power-on. The APW8815 has a 1.2ms digital soft-start and built-in an integrated output discharge device for soft-stop. An internal integrated soft-start ramps up the output voltage with programmable slew rate to reduce the start-up current. A soft-stop function actively discharges the output capacitors.

The APW8815 is available in 14pin TSSOP, 14pin QFN and 16pin TQFN packages respectively.

Simplified Application Circuit



Pin Configuration



TSSOP-14
(Top View)

QFN3.5x3.5-14
(Top View)

TQFN3x3-16
(Top View)

Ordering and Marking Information

APW8815 □□□-□□□ Assembly Material Handling Code Temperature Range Package Code	Package Code O : TSSOP-14 QA : QFN3.5x3.5-14 QB : TQFN3x3-16 Temperature Range I : -40 to 85 °C Handling Code TR : Tape & Reel Assembly Material G : Halogen and Lead Free Device
APW8815 O : APW8815 XXXXX	XXXXX - Date Code
APW8815 QA : APW 8815 XXXXX	XXXXX - Date Code
APW8815 QB : APW 8815 XXXXX	XXXXX - Date Code

Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. ANPEC defines “Green” to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

Absolute Maximum Ratings (Note 1)

Symbol	Parameter	Rating	Unit
V_{CC}	VCC Supply Voltage (VCC to GND)	-0.3 ~ 7	V
V_{PVCC}	PVCC Supply Voltage (PVCC to GND)	-0.3 ~ 7	V
$V_{BOOT-GND}$	BOOT Supply Voltage (BOOT to GND or PGND)	-0.3 ~ 35	V
V_{BOOT}	BOOT Supply Voltage (BOOT to PHASE)	-0.3 ~ 7	V
	All Other Pins (VOUT, OCSET, TON, EN and FB to GND)	-0.3 ~ V_{CC}+0.3	V
	UGATE Voltage (UGATE to PHASE) <400ns Pulse Width >400ns Pulse Width	 -5 ~ V_{BOOT}+0.3 -0.3 ~ V_{BOOT}+0.3	V
	LGATE Voltage (LGATE to GND) <400ns Pulse Width >400ns Pulse Width	 -5 ~ V_{CC}+0.3 -0.3 ~ V_{CC}+0.3	V
V_{PHASE}	PHASE Voltage (PHASE to GND) <400ns Pulse Width >400ns Pulse Width	 -5 ~ 35 -1 ~ 28	V
V_{POK}	POK Supply Voltage (POK to GND)	-0.3 ~ 7	V
V_{PGND}	PGND to GND Voltage	-0.3 ~ 0.3	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature	-65 ~ 150	°C
T_{SDR}	Maximum Soldering Temperature, 10 Seconds	260	°C

Note 1: Absolute Maximum Ratings are those values beyond which the life of a device may be impaired. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Thermal Characteristics

Symbol	Parameter	Typical Value	Unit
θ_{JA}	Thermal Resistance-Junction to Ambient (Note2) TSSOP-14 QFN3.5x3.5-14 TQFN3x3-16	 100 80 40	°C/W

Note 2: θ_{JA} are measured with the component mounted on a high effective the thermal conductivity test board in free air. The exposed pad of package is soldered directly on the PCB.

Recommended Operating Conditions (Note 3)

Symbol	Parameter	Range	Unit
V_{IN}	Converter Input Voltage	1.8 ~ 28	V
VCC, PVCC	VCC, PVCC Supply Voltage	4.5 ~ 5.5	V
V_{OUT}	Converter Output Voltage	0.75 ~ 5.5	V
T_A	Ambient Temperature	-40 ~ 85	°C
T_J	Junction Temperature	-40 ~ 125	°C

Note 3: Refer to the typical application circuit.

Electrical Characteristics

These specifications apply for T_A=-40°C to +85°C, unless otherwise stated. All typical specifications T_A=+25°C, V_{CC}=5V, V_{PVCC}=5V.

Symbol	Parameter	Test Conditions	APW8815			Unit
			Min.	Typ.	Max.	
VOUT AND VFB VOLTAGE						
V_{OUT}	Output Voltage	Adjustable output range	0.75	-	5.5	V
V_{REF}	Reference Voltage		-	0.75	-	V
	Regulation Accuracy	T_A = 25°C	-0.5	-	+0.5	%
		T_A = 0°C ~ 85°C	-0.8	-	+0.8	%
		T_A = -40°C ~ 85°C	-1.0	-	+1.0	%
I_{FB}	FB Input Bias Current	FB = 0.75V	-	0.02	0.1	µA
R_{DIS}	VOUT Discharge Resistance	EN = 0V, V_{OUT} = 0.5V	-	20	50	Ω
SUPPLY CURRENT						
I_{VCC}	VCC Input Bias Current	VCC Plus PVCC Current, PWM, EN = Float, VFB = 0.77V, PHASE = -0.1V	-	400	750	µA
		VCC Plus PVCC Current, PFM, EN = 5V, VFB = 0.77V, PHASE = 0.5V	-	250	470	µA
I_{VCC_SHDN}	VCC Shutdown Current	EN = GND, VCC = 5V	-	4.5	7.5	µA
I_{VCC_SHDN}	PVCC Shutdown Current	EN = GND, PVCC = 5V	-	0	1.0	µA
ON-TIME TIMER AND INTERNAL SOFT-START						
T_{ONN}	Nominal On Time	V_{PHASE} = 12V, V_{OUT} = 2.5V, R_{TON} = 250kΩ	-	749	-	ns
T_{ONF}	Fast On Time	V_{PHASE} = 12V, V_{OUT} = 2.5V, R_{TON} = 100kΩ	280	330	380	ns
T_{ONS}	Slow On Time	V_{PHASE} = 12V, V_{OUT} = 2.5V, R_{TON} = 400kΩ	-	1170	-	ns
$T_{ON(MIN)}$	Minimum On Time		80	110	140	ns
$T_{OFF(MIN)}$	Minimum Off Time	V_{FB} = 0.7V, V_{PHASE} = -0.1V, OCSET = OPEN	350	450	550	ns
T_{SS}	Internal Soft-Start Time	EN High to V_{OUT} Regulation	0.9	1.2	1.5	ms
GATE DRIVER						
	UG Pull-Up Resistance	BOOT-UG = 0.5V	-	5	7	Ω
	UG Sink Resistance	UG-PHASE = 0.5V	-	1	2.5	Ω
	LG Pull-Up Resistance	PVCC-LG = 0.5V	-	5	7	Ω
	LG Sink Resistance	LG-PGND = 0.5V	-	0.9	2.5	Ω
	UG to LG Dead Time	UG falling to LG rising, no load	-	40	-	ns
	LG to UG Dead Time	LG falling to UG rising, no load	-	40	-	ns
BOOTSTRAP SWITCH						
V_F	Ron	V_{PVCC} - $V_{BOOT-GND}$, I_F = 10mA	-	0.5	0.8	V
I_R	Reverse Leakage	$V_{BOOT-GND}$ = 30V, V_{PHASE} = 25V, V_{PVCC} = 5V	-	-	0.5	µA

Electrical Characteristics (Cont.)

These specifications apply for T_A=-40°C to +85°C, unless otherwise stated. All typical specifications T_A=+25°C, V_{CC}=5V, V_{PVCC}=5V.

Symbol	Parameter	Test Conditions	APW8815			Unit
			Min.	Typ.	Max.	
VCC POR THRESHOLD						
V_{PVCC_THR}	Rising PVCC POR Threshold Voltage		4.2	4.35	4.45	V
V_{VCC_THR}	Rising VCC POR Threshold Voltage		4.2	4.35	4.45	V
	VCC POR Hysteresis		-	100	-	mV
CONTROL INPUTS						
	EN High Threshold		2.5	2.65	2.8	V
	Hysterisis		100	175	225	mV
	EN Float Threshold		1.37	1.95	2.39	V
	EN Low Threshold		0.7	1.0	1.3	V
	Hysterisis		150	200	250	mV
	EN Leakage	EN = 0V	-	0.1	1.0	µA
		EN = 5V	-	-	2.0	
POWER-OK INDICATOR						
V_{POK}	POK Threshold	POK in from Lower (POK Goes High)	87	90	93	%
		POK Low Hysteresis (POK Goes Low)	-	3	-	%
		POK out from Normal (POK Goes Low)	120	125	130	%
I_{POK}	POK Leakage Current	V_{POK} = 5V	-	0.1	1.0	µA
	POK Sink Current	V_{POK} = 0.5V	2.5	7.5	-	mA
	POK Debounce Time		43	63	85	µs
	POK Enable Delay Time	EN High to POK High	1.4	2.0	2.6	ms
CURRENT SENSE						
I_{OCSET}	I_{OCSET} OCP Threshold	I_{OCSET} Sourcing	9	10	11	µA
$T_{CIOCSET}$	I_{OCSET} Temperature Coefficient	On The Basis of 25°C	-	4500	-	ppm/°C
V_{ROCSET}	Current-Limit Threshold Setting Range	$V_{OCSET-GND}$ Voltage, Over All Temperature	30	-	200	mV
	Over Current-Limit Comparator Offset	($V_{OCSET-GND}$-$V_{PGND-PHASE}$) Voltage, $V_{OCSET-GND}$ = 60mV	-10	0	10	mV
	Zero Crossing Comparator Offset	$V_{PGND-PHASE}$ Voltage, EN = 3.3V	-9.5	0.5	10.5	mV
PROTECTION						
V_{UV}	UVP Threshold		60	70	80	%
	UVP Hysteresis		-	3	-	%
	UVP Debounce Interval		-	16	-	µs
	UVP Enable Delay	EN High to UVP Workable	1.4	2	2.6	ms

Electrical Characteristics (Cont.)

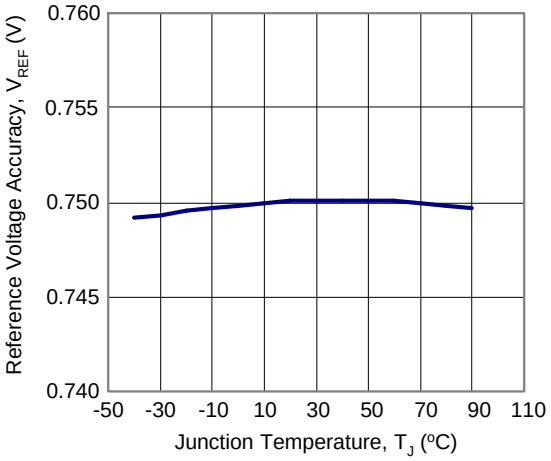
These specifications apply for T_A=-40°C to +85°C, unless otherwise stated. All typical specifications T_A=+25°C, V_{CC}=5V, V_{PVCC}=5V.

Symbol	Parameter	Test Conditions	APW8815			Unit
			Min.	Typ.	Max.	
PROTECTION (CONT.)						
V_{OVR}	OVP Rising Threshold		120	125	130	%
	OVP Propagation Delay	V_{FB} Rising, DV = 10mV	-	1.5	-	µs
T_{OTR}	OTP Rising Threshold (Note 4)		-	160	-	°C
	OTP Hysteresis (Note 4)		-	25	-	°C

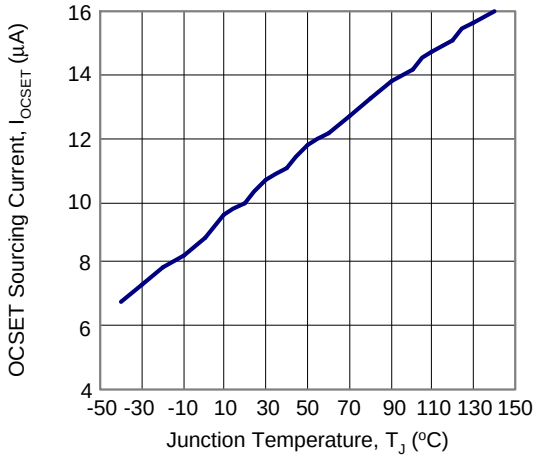
Note 4: Guaranteed by design.

Typical Operating Characteristics

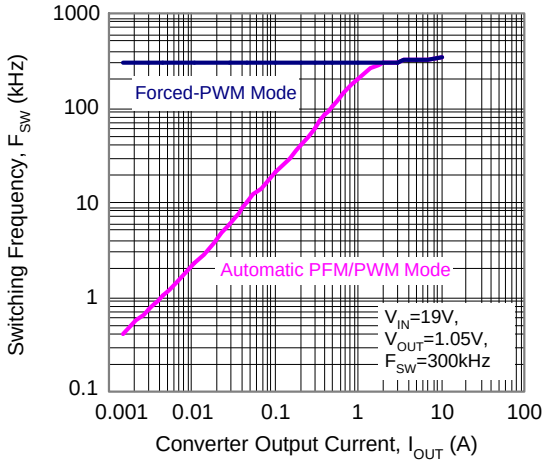
Reference Voltage Accuracy vs. Junction Temperature



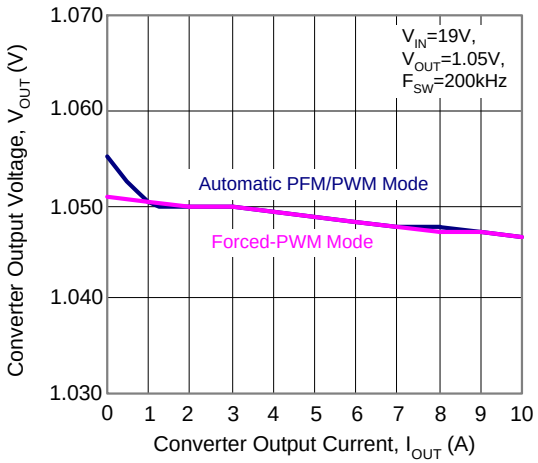
OCSET Sourcing Current vs. Junction Temperature



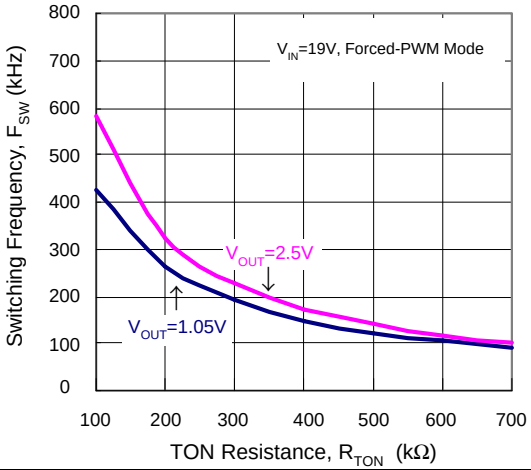
Switching Frequency vs. Converter Output Current



Converter Output Voltage vs. Converter Output Current



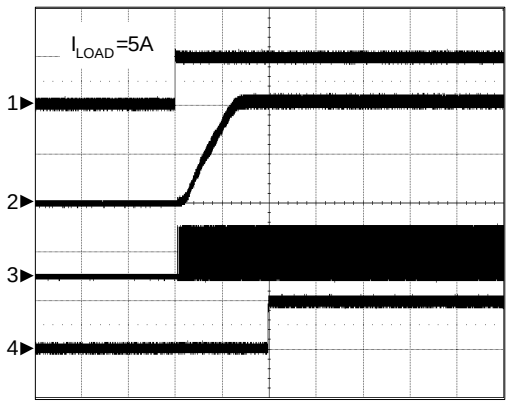
Switching Frequency vs. TON Resistance



Operating Waveforms

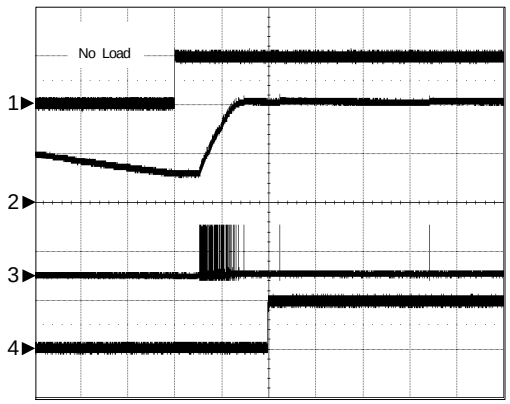
Refer to the typical application circuit. The test condition is V_{IN}=19V, T_A=25°C unless otherwise specified.

Enable at Zero Initial Voltage of V_{OUT}



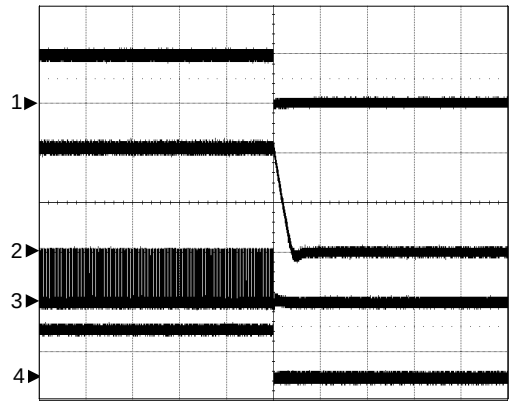
CH1: V_{EN}, 5V/Div, DC
CH2: V_{OUT}, 500mV/Div, DC
CH3: V_{PHASE}, 20V/Div, DC
CH4: V_{POK}, 5V/Div, DC
TIME: 1ms/Div

Enable Before End of Soft-Stop



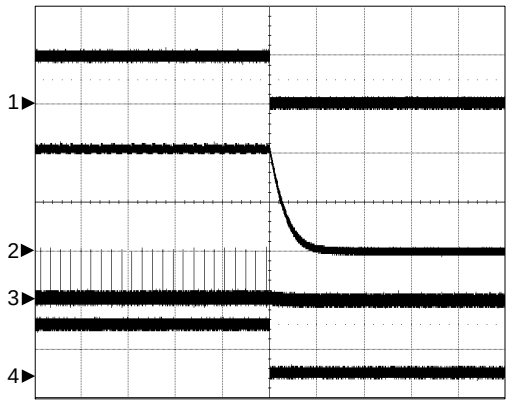
CH1: V_{EN}, 5V/Div, DC
CH2: V_{OUT}, 500mV/Div, DC
CH3: V_{PHASE}, 20V/Div, DC
CH4: V_{POK}, 5V/Div, DC
TIME: 1ms/Div

Shutdown at I_{OUT}=5A



CH1: V_{EN}, 5V/Div, DC
CH2: V_{OUT}, 500mV/Div, DC
CH3: V_{PHASE}, 20V/Div, DC
CH4: V_{POK}, 5V/Div, DC
TIME: 20µs/Div

Shutdown with Soft-Stop at No Load

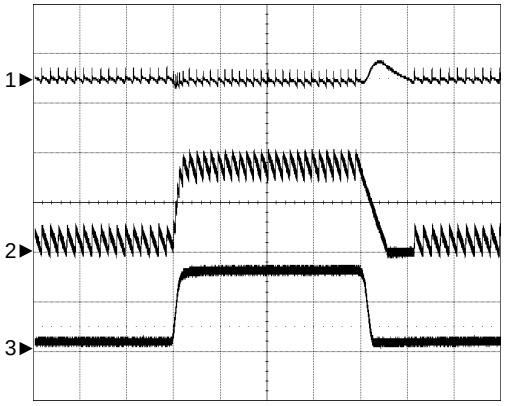


CH1: V_{EN}, 5V/Div, DC
CH2: V_{OUT}, 500mV/Div, DC
CH3: V_{PHASE}, 20V/Div, DC
CH4: V_{POK}, 5V/Div, DC
TIME: 20ms/Div

Operating Waveforms (Cont.)

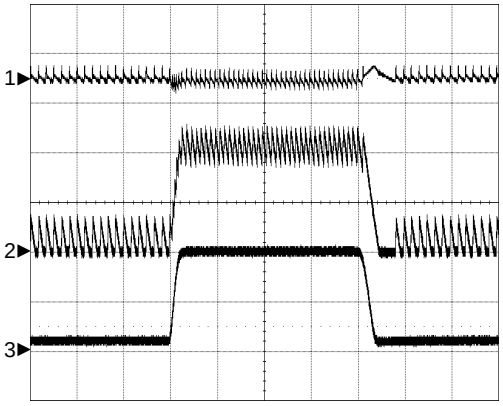
Refer to the typical application circuit. The test condition is V_{IN}=19V, T_A=25°C unless otherwise specified.

Load Transient
V_{OUT}=1.05V, 1A->8A->1A



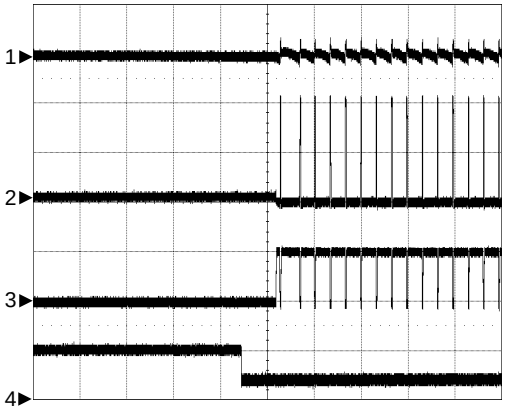
CH1: V_{OUT}, 100mV/Div, AC
CH2: I_L, 5A/Div, DC
CH3: I_{OUT}, 5A/Div, DC
TIME: 20µs/Div

Load Transient
V_{OUT}=2.5V, 1A->10A->1A



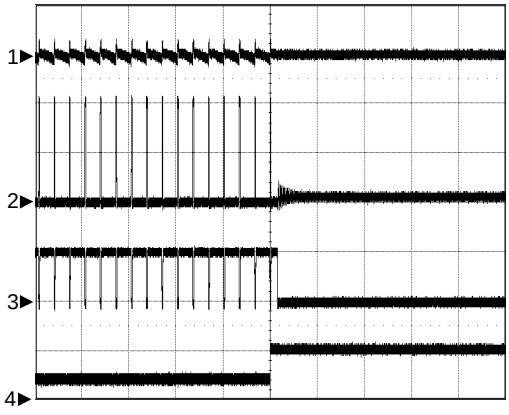
CH1: V_{OUT}, 100mV/Div, AC
CH2: I_L, 5A/Div, DC
CH3: I_{OUT}, 5A/Div, DC
TIME: 20µs/Div

Mode Transient From PFM to PWM



CH1: V_{OUT}, 100mV/Div, AC
CH2: V_{PHASE}, 10V/Div, DC
CH3: V_{LGATE}, 5V/Div, DC
CH4: V_{EN}, 5V/Div, DC
TIME: 10µs/Div

Mode Transient From PWM to PFM

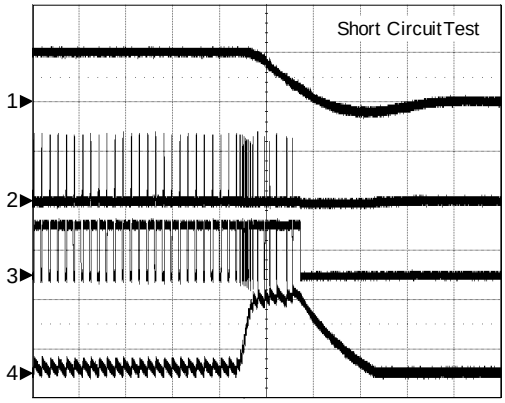


CH1: V_{OUT}, 100mV/Div, AC
CH2: V_{PHASE}, 10V/Div, DC
CH3: V_{LGATE}, 5V/Div, DC
CH4: V_{EN}, 5V/Div, DC
TIME: 10µs/Div

Operating Waveforms (Cont.)

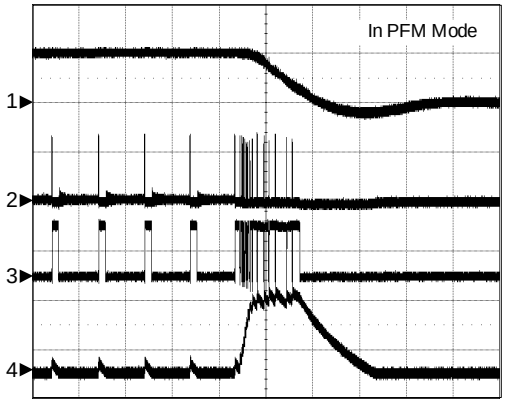
Refer to the typical application circuit. The test condition is V_{IN}=19V, T_A=25°C unless otherwise specified.

Under-Voltage Protection



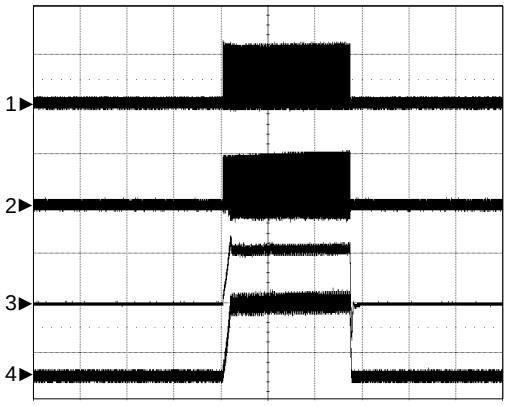
CH1: V_{OUT}, 1V/Div, DC
CH2: V_{UGATE}, 20V/Div, DC
CH3: V_{LGATE}, 5V/Div, DC
CH4: I_L, 10A/Div, DC
TIME: 20µs/Div

Short-Circuit Test



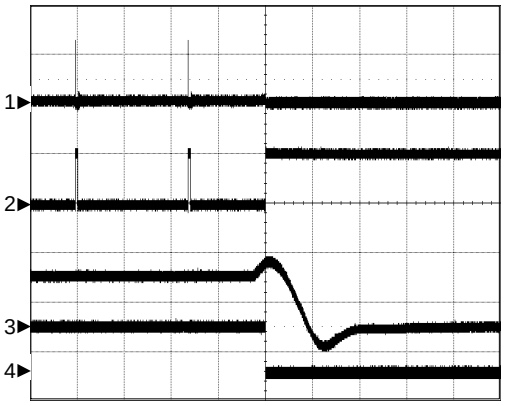
CH1: V_{OUT}, 2V/Div, DC
CH2: V_{UGATE}, 20V/Div, DC
CH3: V_{LGATE}, 5V/Div, DC
CH4: I_L, 10A/Div, DC
TIME: 20µs/Div

Power On in Short-Circuit



CH1: V_{UGATE}, 20V/Div, DC
CH2: V_{LGATE}, 5V/Div, DC
CH3: V_{OUT}, 200mV/Div, DC
CH4: I_L, 10A/Div, DC
TIME: 1ms/Div

Over-Voltage Protection

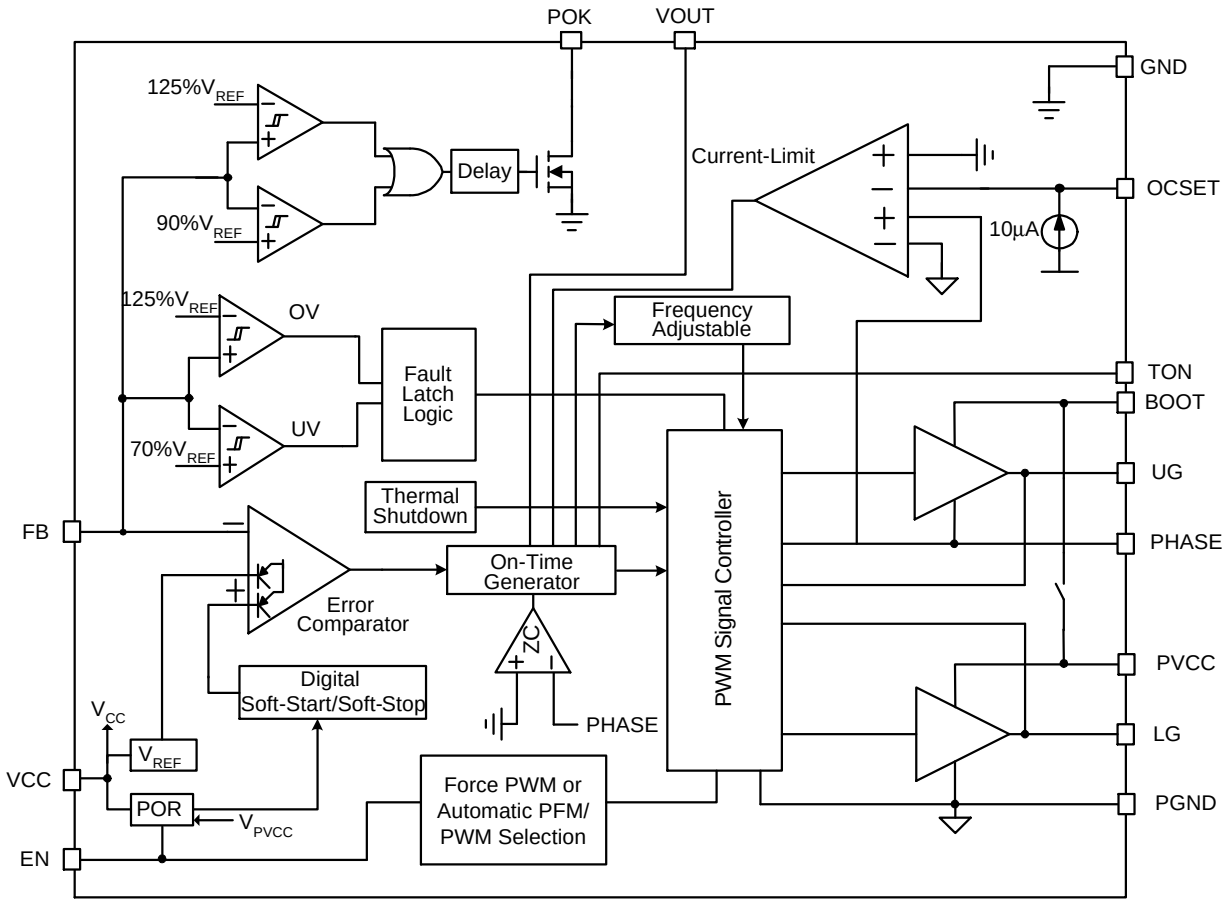


CH1: V_{UGATE}, 20V/Div, DC
CH2: V_{LGATE}, 5V/Div, DC
CH3: V_{OUT}, 1V/Div, DC
CH4: V_{POK}, 5V/Div, DC
TIME: 50µs/Div

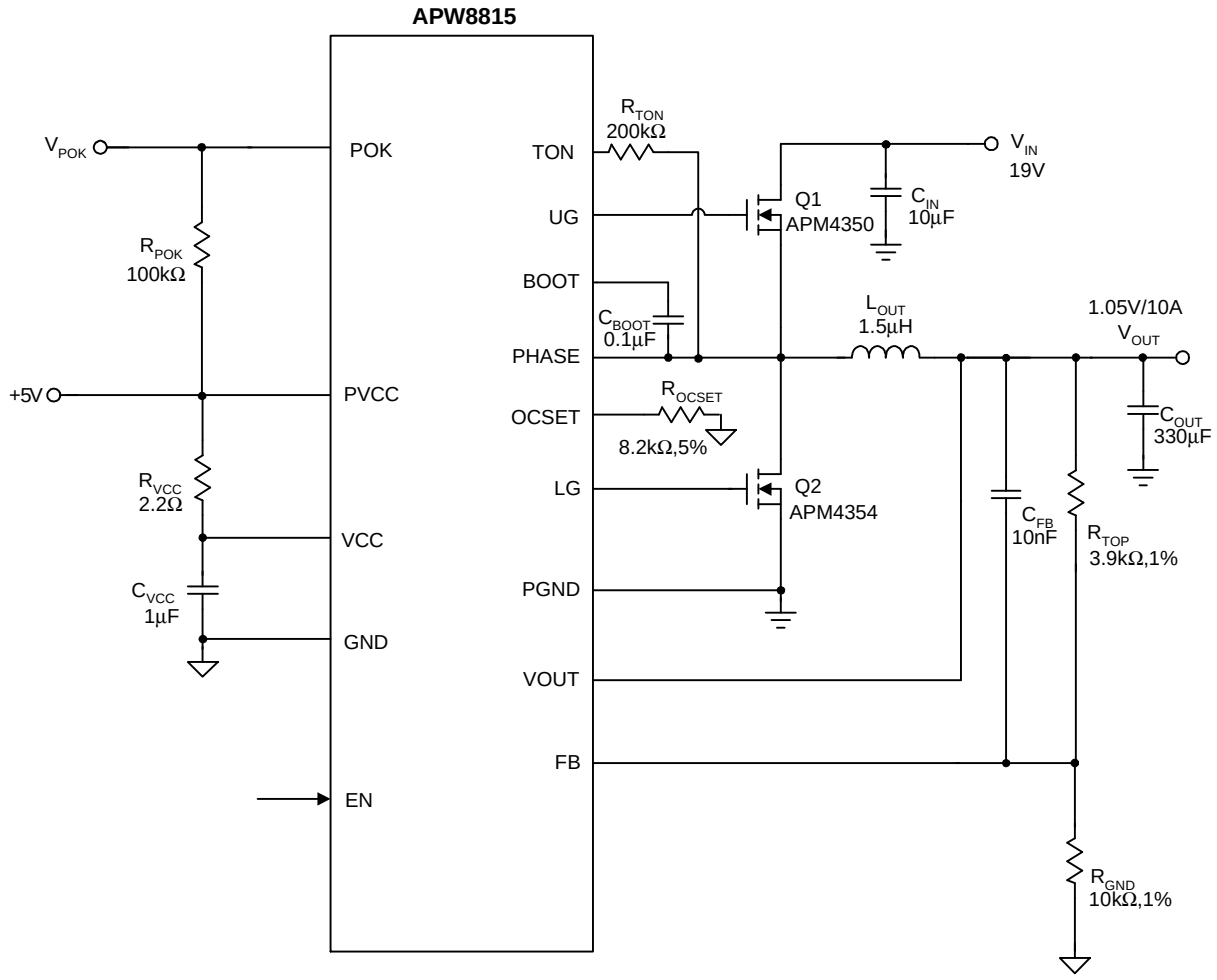
Pin Description

PIN				FUNCTION
NO.			NAME	
TSSOP-14	QFN3.5x3.5 -14	TQFN3x3 -16		
1	1	15	EN	Enable Pin of The PWM Controller. When the EN is above high logic level, the Device is in automatic PFM/PWM Mode. When the EN is floating, the device is in force PWM mode. When the EN is below low logic level, the device is in shutdown and only low leakage current is taken from V_{CC} and V_{IN}.
2	2	16	TON	This Pin is Allowed to Adjust The Switching Frequency. Connect a resistor R_{TON}=100kΩ ~ 600kΩ from TON pin to PHASE pin.
3	3	1	VOUT	The VOUT Pin Makes A Direct Measurement of The Converter Output Voltage. The VOUT pin should be connected to the top feedback resistor at the converter output.
4	4	2	VCC	Supply Voltage Input Pin for Control Circuitry. Connect +5V from the VCC pin to the GND pin. Decoupling at least 1µF of a MLCC capacitor from the VCC pin to the GND pin.
5	5	3	FB	Output Voltage Feedback Pin. This pin is connected to the resistive divider that set the desired output voltage. The POK, UVP, and OVP circuits detect this signal to report output voltage status.
6	6	4	POK	Power Good Output. POK is an open drain output used to indicate the status of the output voltage. Connect the POK in to +5V through a pull-high resistor.
7	7	6	GND	Signal Ground for The IC
8	8	7	PGND	Power Ground of The LG Low-side MOSFET Driver. Connect the pin to the Source of the low-side MOSFET.
9	9	8	LGATE	Output of The Low-side MOSFET Driver. Connect this pin to Gate of the low-side MOSFET. Swings from PGND to VCC.
10	10	9	PVCC	Supply Voltage Input Pin for The LG Low-side MOSFET Gate Driver. Connect +5V from the PVCC pin to the PGND pin. Decoupling at least 1µF of a MLCC capacitor from the PVCC pin to the PGND pin.
11	11	10	OCSET	Current-Limit Threshold Setting Pin. There is an internal source current 10µA through a resistor from OCSET pin to GND. This pin is used to monitor the voltage drop across the Drain and Source of the low-side MOSFET for current-limit
12	12	11	PHASE	Junction Point of The High-side MOSFET Source, Output Filter Inductor And The Low-side MOSFET Drain. Connect this pin to the Source of the high-side MOSFET. PHASE serves as the lower supply rail for the UG high-side gate driver.
13	13	12	UGATE	Output of The High-side MOSFET Driver. Connect this pin to Gate of the high-side MOSFET.
14	14	13	BOOT	Supply Input for The UG Gate Driver And An Internal Level-shift Circuit. Connect to an external capacitor to create a boosted voltage suitable to drive a logic-level N-channel MOSFET.
-	Exposed pad	5,14	NC	No Internal Connection

Block Diagram



Typical Application Circuit



Function Description

Constant-On-Time PWM Controller with Input Feed-Forward

The constant-on-time control architecture is a pseudofixed frequency with input voltage feed-forward. This architecture relies on the output filter capacitor's effective series resistance (ESR) to act as a current-sense resistor, so the output ripple voltage provides the PWM ramp signal. In PFM operation, the high-side switch on-time controlled by the on-time generator is determined solely by a oneshot whose pulse width is inversely proportional to input voltage and directly proportional to output voltage. In PWM operation, the high-side switch on-time is determined by a switching frequency control circuit in the on-time generator block.

The switching frequency control circuit senses the switching frequency of the high-side switch and keeps regulating it at a constant frequency in PWM mode. The design improves the frequency variation and is more outstanding than a conventional constant-on-time controller, which has large switching frequency variation over input voltage, output current, and temperature. Both in PFM and PWM, the on-time generator, which senses input voltage on PHASE pin, provides very fast on-time response to input line transients.

Another one-shot sets a minimum off-time (typical: 450ns). The on-time one-shot is triggered if the error comparator is high, the low-side switch current is below the current-limit threshold, and the minimum off-time oneshot has timed out.

Pulse-Frequency Modulation (PFM)

In PFM mode, an automatic switchover to pulse-frequency modulation (PFM) takes place at light loads. This switchover is affected by a comparator that truncates the low-side switch on-time at the inductor current zero crossing. This mechanism causes the threshold between PFM and PWM operation to coincide with the boundary between continuous and discontinuous inductor-current operation (also known as the critical conduction point).

The on-time of PFM is given by:

$$T_{ON\text{-}PFM} = \frac{1}{F_{SW}} \times \frac{V_{OUT}}{V_{IN}}$$

Where F_{SW} is the nominal switching frequency of the converter in PWM mode.

The load current at handoff from PFM to PWM mode is given by:

$$I_{LOAD(PFM\ to\ PWM)} = \frac{1}{2} \times \frac{V_{IN} - V_{OUT}}{L} \times T_{ON\text{-}PFM}$$
$$= \frac{V_{IN} - V_{OUT}}{2L} \times \frac{1}{F_{SW}} \times \frac{V_{OUT}}{V_{IN}}$$

Forced-PWM Mode

The Forced-PWM mode disables the zero-crossing comparator, which truncates the low-side switch on-time at the inductor current zero crossing. This causes the low-side gate-drive waveform to become the complement of the high-side gate-drive waveform. This in turn causes the inductor current to reverse at light loads while UGATE maintains a duty factor of V_{OUT}/V_{IN}. The benefit of Forced-PWM mode is to keep the switching frequency fairly constant. The Forced-PWM mode is most useful for reducing audio frequency noise, improving load-transient response, and providing sink-current capability for dynamic output voltage adjustment.

Power-On-Reset

A Power-On-Reset (POR) function is designed to prevent wrong logic controls when the PVCC or VCC voltage is low. The POR function continually monitors the bias supply voltage on the PVCC and VCC pins if at least one of the enable pins is set high. When the rising PVCC voltage reaches the rising PVCC POR voltage threshold (4.35V, typical) and the rising VCC voltage reaches the rising VCC POR Threshold (4.35V, typical), the POR signal goes high and the chip initiates soft-start operations. There is almost no hysteresis to POR voltage threshold (about 100mV typical). When PVCC voltage drops lower than 4.25V (typical) or VCC voltage drops lower than 4.25V (typical), the POR disables the chip.

EN Pin Control

When V_{EN} is above the EN high threshold (2.65V, typical), the converter is enabled in automatic PFM/PWM operation mode. When EN pin is floating, APW8815 internal circuit will pull V_{EN} up to 1.95V (Typical). Furthermore, APW8815 is in Forced-PWM operation mode. When V_{EN}

Function Description (Cont.)

EN Pin Control (Cont.)

is below the EN low threshold (1V, typical), the chip is in the shutdown and only low leakage current is taken from VCC.

Digital Soft-Start

The APW8815 integrates digital soft-start circuits to ramp up the output voltage of the converter to the programmed regulation setpoint at a predictable slew rate. The slew rate of output voltage is internally controlled to limit the inrush current through the output capacitors during soft-start process. The figure 1 shows soft-start sequence. When the EN pin is pulled above the rising EN threshold voltage, the device initiates a soft-start process to ramp up the output voltage. The soft-start interval is 1.2ms (typical) and independent of the UGATE switching frequency.

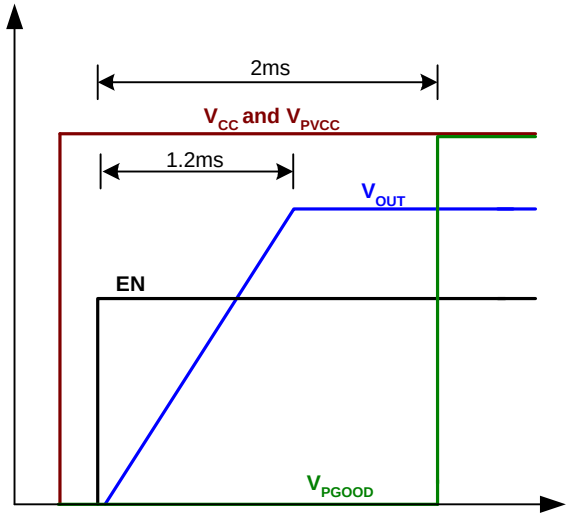


Figure 1. Soft-Start Sequence

During soft-start stage before the PGOOD pin is ready, the under-voltage protection is prohibited. The over-voltage and current-limit protection functions are enabled. If the output capacitor has residue voltage before start-up, both low-side and high-side MOSFETs are in off-state until the internal digital soft-start voltage equals to the V_{FB} voltage. This will ensure that the output voltage starts from its existing voltage level.

In the event of under-voltage, over-voltage, over-temperature, or shutdown, the chip enables the soft-stop function. The soft-stop function discharges the output voltages to the PGND through an internal 20Ω switch.

Power OK Indicator

The APW8815 features an open-drain POK pin to indicate output regulation status. In normal operation, when the output voltage rises 90% of its target value, the POK goes high after 63us internal delay. When the output voltage outruns 70% or 125% of the target voltage, POK signal will be pulled low immediately.

Since the FB pin is used for both feedback and monitoring purposes, the output voltage deviation can be coupled directly to the FB pin by the capacitor in parallel with the voltage divider as shown in the typical applications. In order to prevent false POK from dropping, capacitors need to parallel at the output to confine the voltage deviation with severe load step transient.

Under-Voltage Protection (UVP)

In the operational process, if a short-circuit occurs, the output voltage will drop quickly. When load current is bigger than current-limit threshold value, the output voltage will fall out of the required regulation range. The under-voltage protection circuit continually monitors the FB voltage after soft-start is completed. If a load step is strong enough to pull the output voltage lower than the under-voltage threshold, the under-voltage threshold is 70% of the nominal output voltage, the internal UVP delay counter starts to count. After 16µs debounce time, the device turns off both high-side and low-side MOSEFET with latched and starts a soft-stop process to shut down the output gradually. Toggling enable pin to low or recycling PVCC or VCC, will clear the latch and bring the chip back to operation.

Over-Voltage Protection (OVP)

The over-voltage function monitors the output voltage by FB pin. When the FB voltage increases over 125% of the reference voltage due to the high-side MOSFET failure or for other reasons, the over-voltage protection comparator designed with a 1.5µs noise filter will force the low-side MOSFET gate driver fully turn on and latch high. This

Function Description (Cont.)

Over-Voltage Protection (OVP) (Cont.)

action actively pulls down the output voltage. In the meantime, the output voltage is also pulled low by internal discharge transistor.

This OVP scheme only clamps the voltage overshoot and does not invert the output voltage when otherwise activated with a continuously high output from low-side MOSFET driver. It's a common problem for OVP schemes with a latch. Once an over-voltage fault condition is set, it can only be reset by toggling EN, PVCC or VCC poweron-reset signal.

Current-Limit

The current-limit circuit employs a "valley" current-sensing algorithm (See Figure 2). The APW8815 uses the low-side MOSFET's $R_{DS(ON)}$ of the synchronous rectifier as a current-sensing element. If the magnitude of the current-sense signal at PHASE pin is above the current-limit threshold, the PWM is not allowed to initiate a new cycle. The actual peak current is greater than the current-limit threshold by an amount equals to the inductor ripple current. Therefore, the exact current-limit characteristic and maximum load capability are the functions of the sense resistance, inductor value, and input voltage.

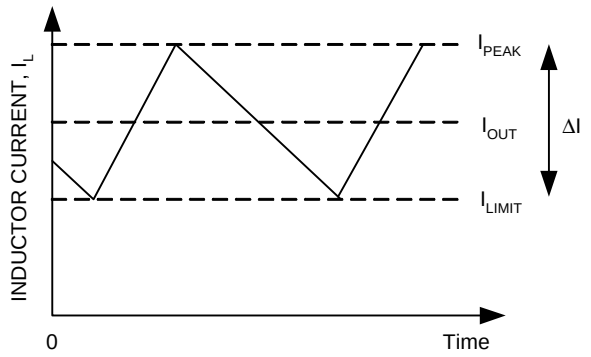


Figure 2. Current-Limit Algorithm

The PWM controller uses the low-side MOSFETs on-resistance $R_{DS(ON)}$ to monitor the current for protection against shortened outputs. The MOSFET's $R_{DS(ON)}$ is varied by temperature and gate to source voltage, the user should determine the maximum $R_{DS(ON)}$ in manufacture's datasheet.

The OCSET pin can source 10μA through an external resistor for adjusting current-limit threshold. The voltage at OCSET pin is equal to 10μA x R_{OCSET}. The relationship between the sampled voltage V_{OCSET} and the current-limit threshold I_{LIMIT} is given by:

$$10\mu A \times R_{OCSET} = I_{LIMIT} \times R_{DS(ON)}$$

Where R_{OCSET} is the resistor of current-limit setting threshold. $R_{DS(ON)}$ is the low side MOSFETs conducive resistance. I_{LIMIT} is the setting current-limit threshold. I_{LIMIT} can be expressed as I_{OUT} minus half of peak-to-peak inductor current.

The PCB layout guidelines should ensure that noise and DC errors do not corrupt the current-sense signals at PHASE. Place the hottest power MOSEFTs as close to the IC as possible for best thermal coupling. When combined with the under-voltage protection circuit, this current-limit method is effective in almost every circumstance.

Over-Temperature Protection (OTP)

When the junction temperature increases above the rising threshold temperature T_{OTR}, the IC will enter the over-temperature protection state that suspends the PWM, which forces the UGATE and LGATE gate drivers output low. The thermal sensor allows the converters to start a start-up process and regulate the output voltage again after the junction temperature cools by 25°C. The OTP is designed with a 25°C hysteresis to lower the average T_J during continuous thermal overload conditions, which increases lifetime of the APW8815.

Programming the On-Time Control and PWM Switching Frequency

The APW8815 does not use a clock signal to produce PWM. The device uses the constant-on-time control architecture to produce pseudo-fixed frequency with input voltage feed-forward. The on-time pulse width is proportional to output voltage V_{OUT} and inverses proportional to input voltage V_{IN}. In PWM, the on-time calculation is written as below :

$$T_{ON} = 19 \times 10^{-12} \times R_{TON} \left[\frac{\left(\frac{2}{3}\right) V_{OUT} + 0.1V}{V_{IN}} \right] + 50ns$$

Where:

R_{TON} is the resistor connected from TON pin to PHASE

Function Description (Cont.)

Programming the On-Time Control and PWM Switching Frequency (Cont.)

pin. Furthermore, the approximate PWM switching frequency is written as :

$$T_{ON} = \frac{D}{F_{SW}} \Rightarrow F_{SW} = \frac{V_{OUT} / V_{IN}}{T_{ON}}$$

Where:

F_{SW} is the PWM switching frequency.

APW8815 doesn't have VIN pin to calculate on-time pulse width. Therefore, monitoring V_{PHASE} voltage as input voltage to calculate on-time when the high-side MOSFET is turned on. And then, use the relationship between ontime and duty cycle to obtain the switching frequency. The curve below is the relationship between R_{TON} and the switching frequency F_{SW}.

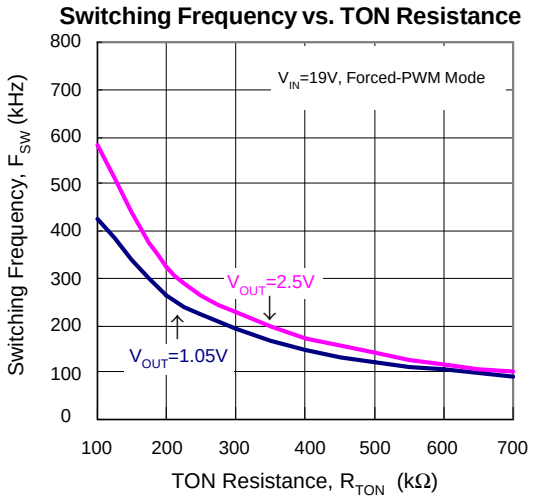


Figure 3.

Application Information

Output Voltage Setting

The output voltage is adjustable from 0.75V to 5.5V with a resistor-divider connected with FB, GND, and converter's output. Using 1% or better resistors for the resistor-divider is recommended. The output voltage is determined by:

$$V_{OUT} = 0.75 \times \left(1 + \frac{R_{TOP}}{R_{GND}}\right)$$

Where 0.75 is the reference voltage, R_{TOP} is the resistor connected from converter's output to FB, and R_{GND} is the resistor connected from FB to GND. Suggested R_{GND} is in the range from 1k to 20kΩ. To prevent stray pickup, locate resistors R_{TOP} and R_{GND} close to APW8815.

Output Inductor Selection

The duty cycle (D) of a buck converter is the function of the input voltage and output voltage. Once an output voltage is fixed, it can be written as:

$$D = \frac{V_{OUT}}{V_{IN}}$$

The inductor value (L) determines the inductor ripple current, I_{RIPPLE}, and affects the load transient reponse. Higher inductor value reduces the inductor's ripple current and induces lower output ripple voltage. The ripple current and ripple voltage can be approximated by:

$$I_{RIPPLE} = \frac{V_{IN} - V_{OUT}}{F_{SW} \times L} \times \frac{V_{OUT}}{V_{IN}}$$

Where F_{SW} is the switching frequency of the regulator. Although the inductor value and frequency are increased and the ripple current and voltage are reduced, a tradeoff exists between the inductor's ripple current and the regulator load transient response time.

A smaller inductor will give the regulator a faster load transient response at the expense of higher ripple current. Increasing the switching frequency (F_{SW}) also reduces the ripple current and voltage, but it will increase the switching loss of the MOSFETs and the power dissipation of the converter. The maximum ripple current occurs at the maximum input voltage. A good starting point is to choose the ripple current to be approximately 30% of the maximum output current. Once the inductance value has been chosen, selecting an inductor which is capable of carrying the required peak current without going into saturation. In some types of inductors, especially core that is made of ferrite, the ripple current will increase abruptly when it saturates. This results in a larger output ripple voltage. Besides, the inductor needs to have low DCR to reduce the loss of efficiency.

Output Capacitor Selection

Output voltage ripple and the transient voltage deviation are factors which have to be taken into consideration when selecting an output capacitor. Higher capacitor value and lower ESR reduce the output ripple and the load transient drop. Therefore, selecting high performance low ESR capacitors is recommended for switching regulator applications. In addition to high frequency noise related to MOSFET turn-on and turn-off, the output voltage ripple includes the capacitance voltage drop ΔV_{COUT} and ESR voltage drop ΔV_{ESR} caused by the AC peak-to-peak inductor's current. These two voltages can be represented by:

$$\Delta V_{COUT} = \frac{I_{RIPPLE}}{8 C_{OUT} F_{SW}}$$

$$\Delta V_{ESR} = I_{RIPPLE} \times R_{ESR}$$

These two components constitute a large portion of the total output voltage ripple. In some applications, multiple capacitors have to be paralleled to achieve the desired ESR value. If the output of the converter has to support another load with high pulsating current, more capacitors are needed in order to reduce the equivalent ESR and suppress the voltage ripple to a tolerable level. A small decoupling capacitor (1μF) in parallel for bypassing the noise is also recommended, and the voltage rating of the output capacitors are also must be considered. To support a load transient that is faster than the switching frequency, more capacitors are needed for reducing the voltage excursion during load step change. Another aspect of the capacitor selection is that the total AC current going through the capacitors has to be less than the rated RMS current specified on the capacitors in order to prevent the capacitor from over-heating.

Input Capacitor Selection

The input capacitor is chosen based on the voltage rating and the RMS current rating. For reliable operation, selecting the capacitor voltage rating to be at least 1.3 times

Application Information (Cont.)

Input Capacitor Selection (Cont.)

higher than the maximum input voltage. The maximum RMS current rating requirement is approximately $I_{OUT}/2$, where I_{OUT} is the load current. During power-up, the input capacitors have to handle great amount of surge current. For low-duty notebook appliactions, ceramic capacitor is recommended. The capacitors must be connected between the drain of high-side MOSFET and the source of low-side MOSFET with very low-impeadance PCB layout.

MOSFET Selection

The application for a notebook battery with a maximum voltage of 24V, at least a minimum 30V MOSFETs should be used. The design has to trade off the gate charge with the $R_{DS(ON)}$ of the MOSFET:

· For the low-side MOSFET, before it is turned on, the body diode has been conducting. The low-side MOSFET driver will not charge the miller capacitor of this MOSFET.

· In the turning off process of the low-side MOSFET, the load current will shift to the body diode first. The high dv/dt of the phase node voltage will charge the miller capacitor through the low-side MOSFET driver sinking current path. This results in much less switching loss of the low-side MOSFETs. The duty cycle is often very small in high battery voltage applications, and the low-side MOSFET will conduct most of the switching cycle; therefore, when using smaller $R_{DS(ON)}$ of the low-side MOSFET, the converter can reduce power loss. The gate charge for this MOSFET is usually the secondary consideration. The high-side MOSFET does not have this zero voltage switching condition; in addition, because it conducts for less time compared to the low-side MOSFET, the switching loss tends to be dominant. Priority should be given to the MOSFETs with less gate charge, so that both the gate driver loss and switching loss will be minimized.

The selection of the N-channel power MOSFETs are determined by the $R_{DS(ON)}$, reversing transfer capacitance (C_{RSS}) and maximum output current requirement. The losses in the MOSFETs have two components: conduction loss and transition loss. For the high-side and low-side MOSFETs, the losses are approximately given by the following equations:

$$P_{high\text{-}side} = I_{OUT}^{2}(1+TC)(R_{DS(ON)})D + (0.5)(I_{OUT})(V_{IN})(t_{SW})F_{SW}$$

$$P_{low\text{-}side} = I_{OUT}^{2}(1+TC)(R_{DS(ON)})(1-D)$$

Where

I_{OUT} is the load current

TC is the temperature dependency of $R_{DS(ON)}$

F_{SW} is the switching frequency

t_{SW} is the switching interval

D is the duty cycle

Note that both MOSFETs have conduction losses while the high-side MOSFET includes an additional transition loss. The switching interval, t_{SW}, is the function of the reverse transfer capacitance C_{RSS}. The (1+TC) term is a factor in the temperature dependency of the $R_{DS(ON)}$ and can be extracted from the "$R_{DS(ON)}$ vs. Temperature" curve of the power MOSFET.

Layout Consideration

In any high switching frequency converter, a correct layout is important to ensure proper operation of the regulator. With power devices switching at higher frequency, the resulting current transient will cause voltage spike across the interconnecting impedance and parasitic circuit elements. As an example, consider the turn-off transition of the PWM MOSFET. Before turn-off condition, the MOSFET is carrying the full load current. During turn-off, current stops flowing in the MOSFET and is freewheeling by the low side MOSFET and parasitic diode. Any parasitic inductance of the circuit generates a large voltage spike during the switching interval. In general, using short and wide printed circuit traces should minimize interconnecting impedances and the magnitude of voltage spike. Besides, signal and power grounds are to be kept separating and finally combined using ground plane construction or single point grounding. The best tie-point between the signal ground and the power ground is at the negative side of the output capacitor on each channel, where there is less noise. Noisy traces beneath the IC are not recommended. Below is a checklist for your layout:

· Keep the switching nodes (UGATE, LGATE, BOOT, and PHASE) away from sensitive small signal nodes since these nodes are fast moving signals.

Therefore, keep traces to these nodes as short as possible and there should be no other weak signal traces in parallel with theses traces on any layer.

Application Information (Cont.)

Layout Consideration (Cont.)

· The signals going through theses traces have both high dv/dt and high di/dt with high peak charging and discharging current. The traces from the gate drivers to the MOSFETs (UGATE and LGATE) should be short and wide.

· Place the source of the high-side MOSFET and the drain of the low-side MOSFET as close as possible. Minimizing the impedance with wide layout plane between the two pads reduces the voltage bounce of the node. In addition, the large layout plane between the drain of the MOSFETs (V_{IN} and PHASE nodes) can get better heat sinking.

· The PGND is the current sensing circuit reference ground and also the power ground of the LGATE low-side MOSFET. On the hand, the PGND trace should be a separate trace and independently go to the source of the low-side MOSFET. Besides, the current sense resistor should be close to OCSET pin to avoid parasitic capacitor effect and noise coupling.

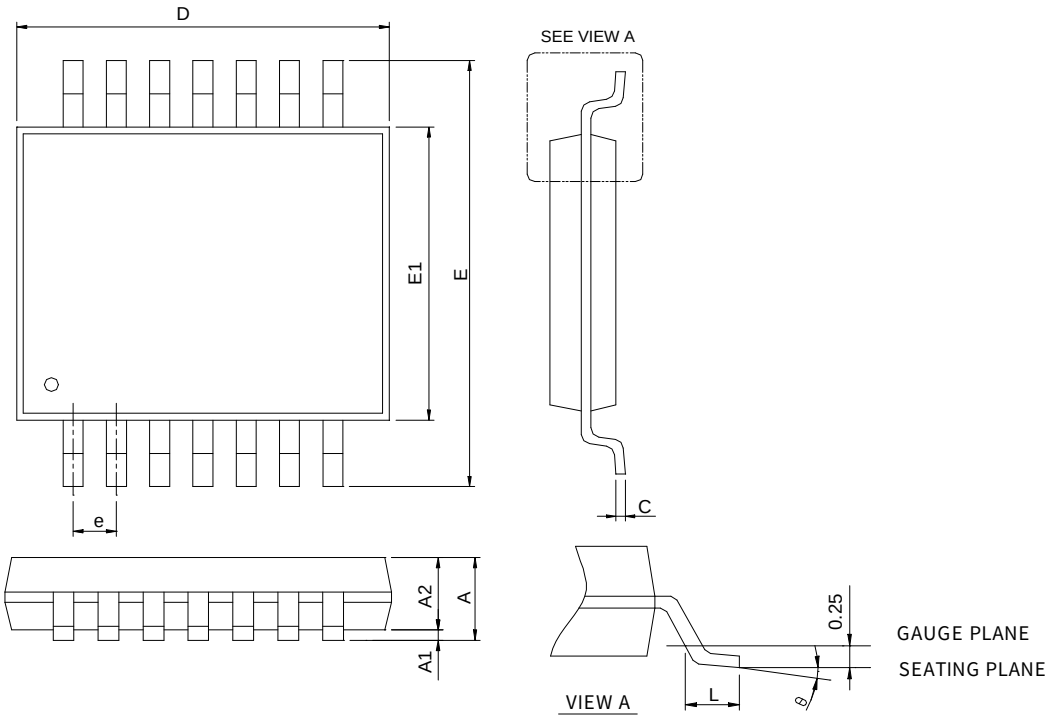
· Decoupling capacitors, the resistor-divider, and boot capacitor should be close to their pins. (For example, place the decoupling ceramic capacitor close to the drain of the high-side MOSFET as close as possible.)

· The input bulk capacitors should be close to the drain of the high-side MOSFET, and the output bulk capacitors should be close to the loads. The input capacitor's ground should be close to the grounds of the output capacitors and low-side MOSFET.

· Locate the resistor-divider close to the FB pin to minimize the high impedance trace. In addition, FB pin traces can't be close to the switching signal traces (UGATE, LGATE, BOOT, and PHASE).

Package Information

TSSOP-14

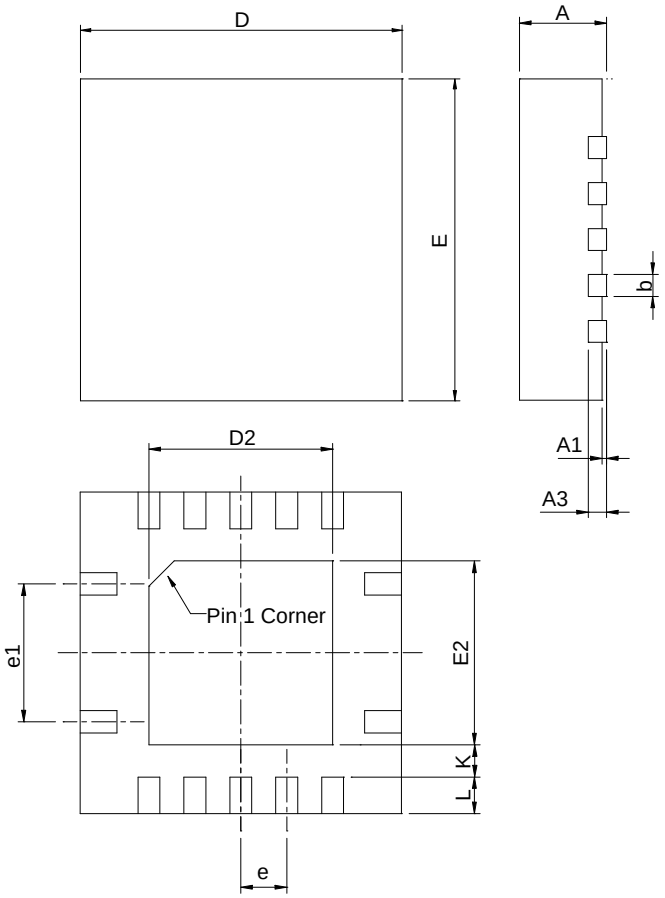


SYMBOL	TSSOP-14			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A		1.20		0.047
A1	0.05	0.15	0.002	0.006
A2	0.80	1.05	0.031	0.041
b	0.19	0.30	0.007	0.012
c	0.09	0.20	0.004	0.008
D	4.90	5.10	0.193	0.201
E	6.20	6.60	0.244	0.260
E1	4.30	4.50	0.169	0.177
e	0.65 BSC		0.026 BSC	
L	0.45	0.75	0.018	0.030
θ	0°	8°	0°	8°

Note : 1. Follow from JEDEC MO-153 AB-1.
2. Dimension "D" does not include mold flash, protrusions or gate burrs.
Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
3. Dimension "E1" does not include inter-lead flash or protrusions.
Inter-lead flash and protrusions shall not exceed 10 mil per side.

Package Information

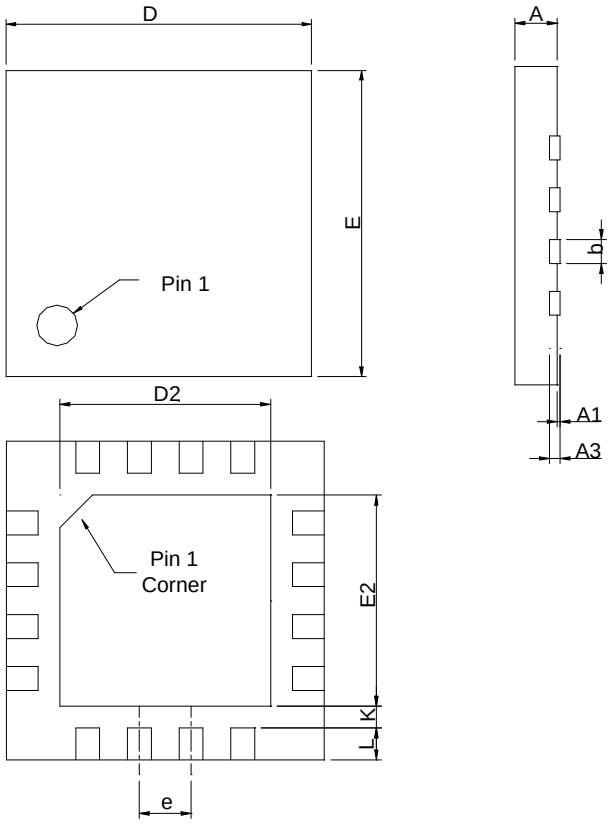
QFN3.5x3.5-14



SYMBOL	QFN3.5x3.5-14			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.80	1.00	0.031	0.039
A1	0.00	0.05	0.000	0.002
A3	0.20 REF		0.008 REF	
b	0.18	0.30	0.007	0.012
D	3.40	3.60	0.134	0.142
D2	1.60	2.20	0.063	0.087
E	3.40	3.60	0.134	0.142
E2	1.60	2.20	0.063	0.087
e	0.50 BSC		0.020 BSC	
e1	1.50 BSC		0.059 BSC	
L	0.30	0.50	0.012	0.020
K	0.20		0.008	

Package Information

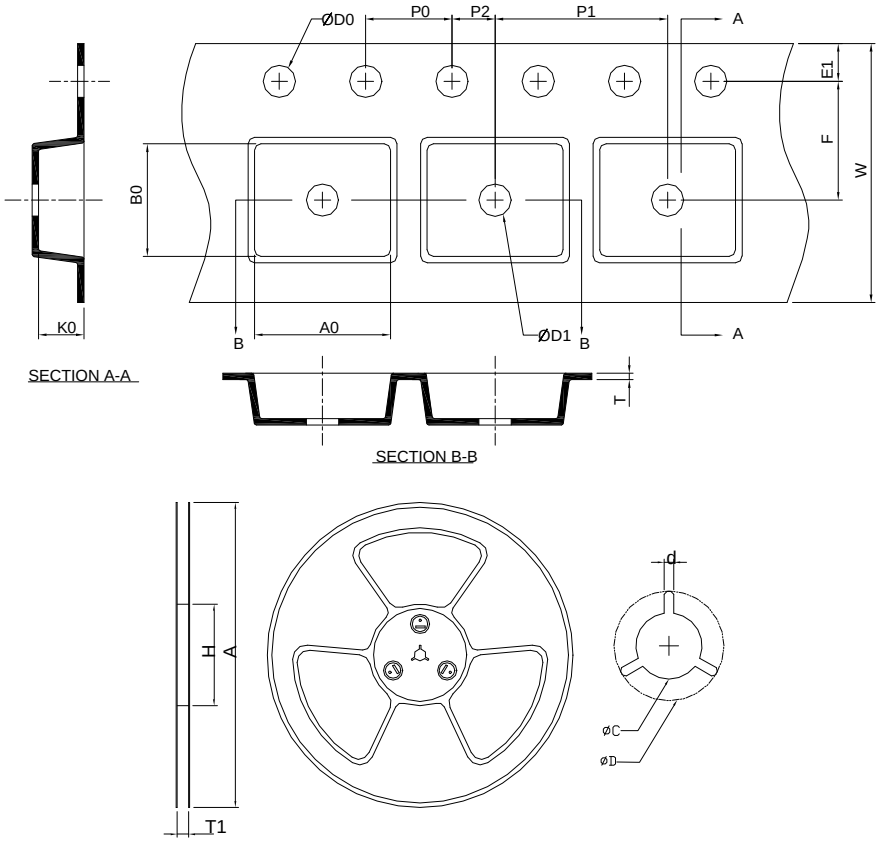
TQFN3x3-16



SYMBOL	TQFN3x3-16			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	0.80	0.028	0.031
A1	0.00	0.05	0.000	0.002
A3	0.20 REF		0.008 REF	
b	0.18	0.30	0.007	0.012
D	2.90	3.10	0.114	0.122
D2	1.50	1.80	0.059	0.071
E	2.90	3.10	0.114	0.122
E2	1.50	1.80	0.059	0.071
e	0.50 BSC		0.020 BSC	
L	0.30	0.50	0.012	0.020
K	0.20		0.008	

Note : Follow JEDEC MO-220 WEED-4.

Carrier Tape & Reel Dimensions



Application	A	H	T1	C	d	D	W	E1	F
TSSOP-14	330.0±2.00	50 MIN.	16.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0±0.30	1.75±0.10	5.50±0.10
	P0	**P1**	**P2**	**D0**	**D1**	**T**	**A0**	**B0**	**K0**
	4.00±0.10	8.00±0.10	2.00±0.10	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.40±0.20	5.20±0.20	1.60±0.20
Application	**A**	**H**	**T1**	**C**	**d**	**D**	**W**	**E1**	**F**
QFN3.5x3.5-14	330.0±2.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0±0.30	1.75±0.10	5.5±0.10
	P0	**P1**	**P2**	**D0**	**D1**	**T**	**A0**	**B0**	**K0**
	4.0±0.10	8.0±0.10	2.0±0.10	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	4.35±0.20	4.35±0.20	1.1±0.20
Application	**A**	**H**	**T1**	**C**	**d**	**D**	**W**	**E1**	**F**
TQFN3x3-16	330±2.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0±0.30	1.75±0.10	5.5±0.05
	P0	**P1**	**P2**	**D0**	**D1**	**T**	**A0**	**B0**	**K0**
	4.0±0.10	8.0±0.10	2.0±0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	3.30±0.20	3.30±0.20	1.30±0.20

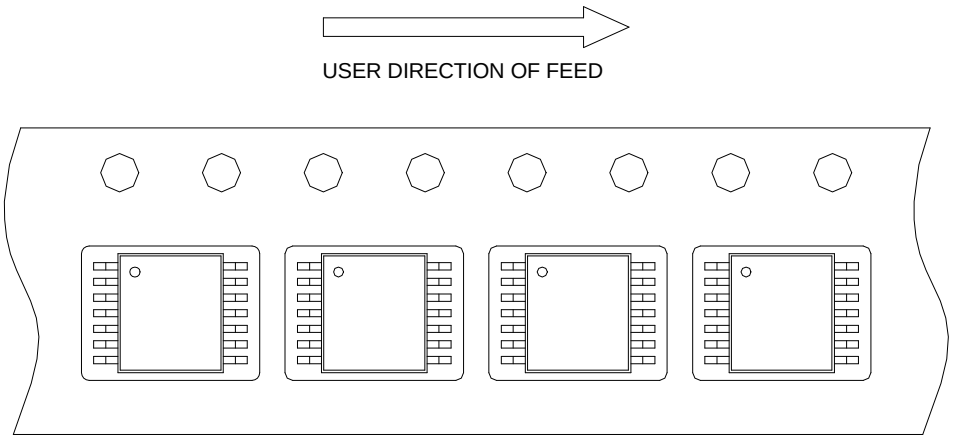
(mm)

Devices Per Unit

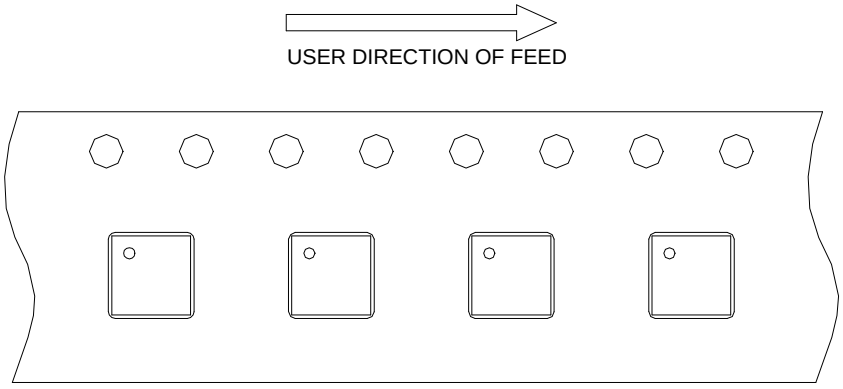
Package Type	Unit	Quantity
TSSOP-14	Tape & Reel	2500
QFN3.5x3.5-14	Tape & Reel	3000
TQFN3x3-16	Tape & Reel	3000

Taping Direction Information

TSSOP-14

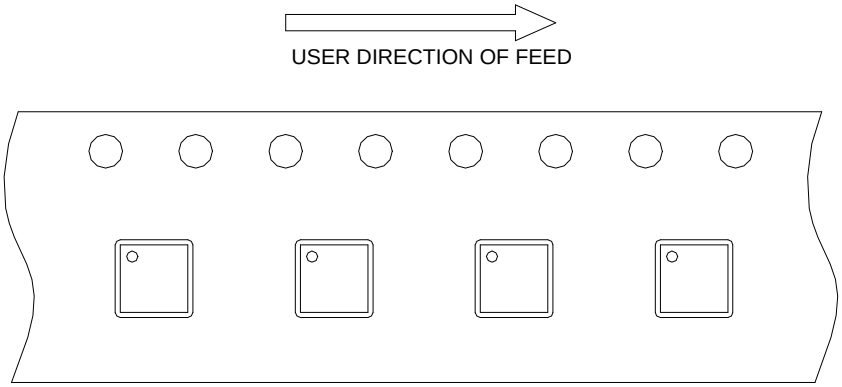


QFN3.5x3.5-14

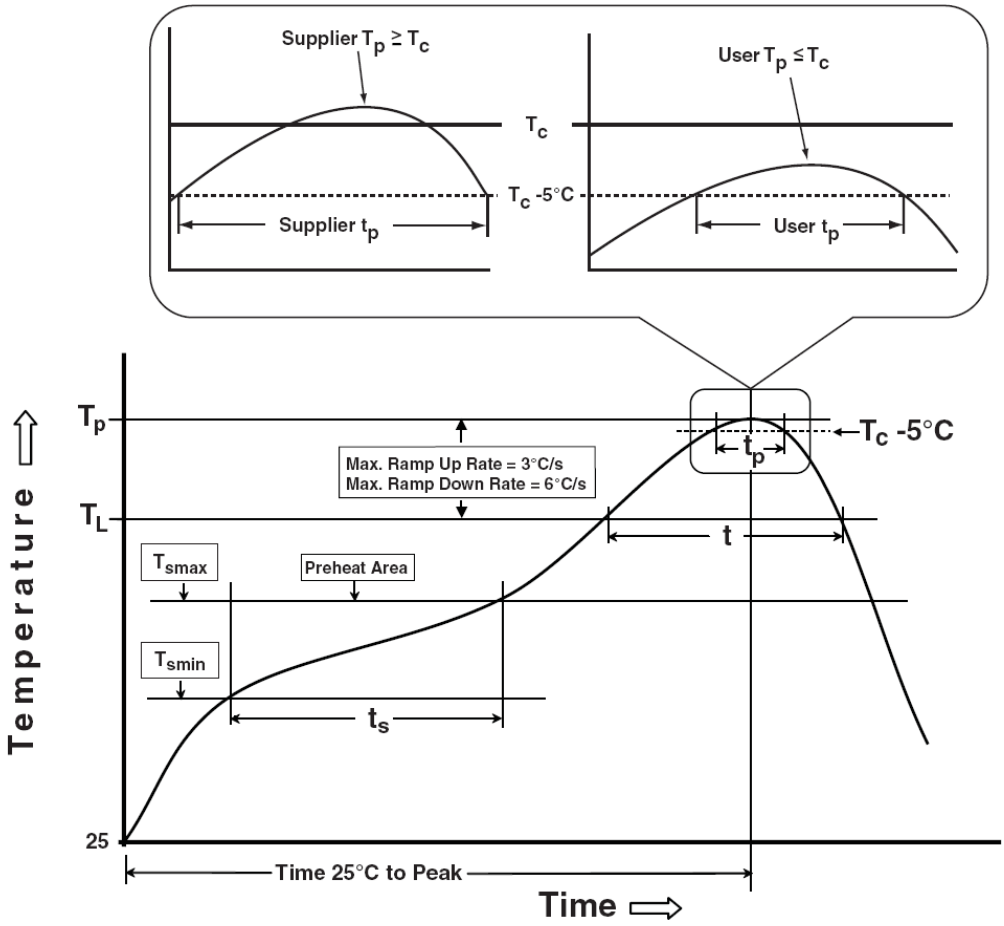


Taping Direction Information

TQFN3x3-16



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	 100 °C 150 °C 60-120 seconds	 150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 ³350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 350-2000	Volume mm^3 >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HOLT	JESD-22, A108	1000 Hrs, Bias @ T_j=125°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C
HBM	MIL-STD-883-3015.7	VHBM≧2KV
MM	JESD-22, A115	VMM≧200V
Latch-Up	JESD 78	10ms, 1_{tr}≧100mA

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